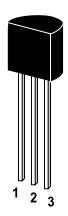
NPN Silicon Epitaxial Planar Transistor

High frequency low noise amplifier application HF band amplifier application

The transistor is subdivided into three groups R, O and Y, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings $(T_a = 25^{\circ}C)$

	Symbol	Value	Unit			
Collector Base Voltage	V _{CBO}	35	V			
Collector Emitter Voltage	V _{CEO}	30	V			
Emitter Base Voltage	V _{EBO}	4	V			
Collector Current	Ic	100	mA			
Emitter Current	I _E	-100	mA			
Power Dissipation	P _{tot}	400	mW			
Junction Temperature	T _j	125	°С			
Storage Temperature Range	T _S	-55 to +125	°С			







ST 2SC3190

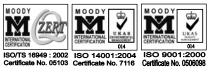
Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =12V, I _C =2mA					
Current Gain Group R	h _{FE}	40	-	80	-
0	h _{FE}	70	-	140	-
Υ	h _{FE}	120	-	240	-
Collector Cutoff Current					
at V _{CB} =20V	I _{CBO}	-	-	0.1	μΑ
Emitter Cutoff Current					
at V _{EB} =2V	I _{EBO}	-	-	1	μΑ
Collector Saturation Voltage					
at I _C =10mA, I _B =1mA	$V_{CE(sat)}$	-	-	0.4	V
Base Emitter Saturation Voltage					
at I _C =10mA, I _B =1mA	$V_{BE(sat)}$	-	-	1	V
Transition Frequency					
at V _{CE} =10V, I _C =2mA	f _T	80	120	-	MHz
Reverse Transfer Capacitance					
at V _{CE} =10V, f=1MHz	Cre	-	2.2	3	pF
Collector Base Time Constant					
at V _{CE} =10V, I _E =-1mA, f=30MHz	C _{c,} rbb	-	30	50	ps
Noise Figure					
at V_{CE} =10V, f=1MHz, I_{E} =-1mA, R_{g} =50 ς	NF	-	2	3.5	dB









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